Electronic Supplementary Information

An Ultraviolet Excitation Anti-Counterfeiting Materials of Sb³⁺

Doped Cs₂ZrCl₆ Vacancy-Ordered Double Perovskite

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Figure S1. (a) PLE and (b) PL spectra of 1% Sb³⁺ doped Cs₂ZrCl₆ (monitoring at emission wavelength of 495 nm and 610 nm, excited by 285 nm).

Table S1. EDS results (atom%) from the points on the selected 10% Sb³⁺ doped Cs_2ZrCl_6 particle.

Element	Cs	Zr	Sb	Cl
Proportion	23.70	13.15	3.26	59.89

feed ratio	ICP-OES results
1%	0.34%
4%	1.61%
7%	2.94%
10%	3.53%
15%	4.36%
20%	5.72%

Table S2. feed ratio and ICP-OES results of Sb/(Sb + Zr).



Figure S2. Time-resolved PL spectra of Cs_2ZrCl_6 , $\lambda_{ex} = 258$ nm, $\lambda_{em} = 447$ nm.

Wavelength	Lifetime	$ au_{ave}$
258 nm and 447 nm	1.05 µs (63.28%) 11.29 µs (36.72%)	2.41 µs
285 nm and 610 nm	8.57 μs	
325 nm and 496 nm	1.00 µs (35.97%) 9.86 µs (64.03%)	3.34 µs
365 nm and 610 nm	10.50 µs	

Table S3. PL lifetime of 10% Sb³⁺ doped Cs₂ZrCl₆.



Figure S3. (a) Wavelength-dependent PL spectra and (b) CIE color coordinates of 1% Sb^{3+} doped Cs_2ZrCl_6 at different excitation wavelengths for 1% Sb^{3+} doped Cs_2ZrCl_6 .



Figure S4. PL intensity of 10% Sb^{3+} doped Cs_2ZrCl_6 for fresh and 100 days under natural conditions.



Figure S5. (a) Emission spectra of the fresh 10% Sb³⁺ doped Cs₂ZrCl₆ after water vapor treatment at different times (relative humidity maintained at 100%). (b) The PL intensity of the samples changes.